

PNP EPITAXIAL SILICON TRANSISTOR

Features

- Excellent HFE Linearity HFE
- hFE(2)=25(Min.) at VCE=6V, Ic=400m
- High Total Power Dissipation: Pc=225mW
- RoHS compliant package

Mechanical Data

- Case: SOT-23 Molded plastic
- Epoxy: UL94V-O rate flame retardant

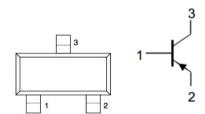
Packing & Order Information

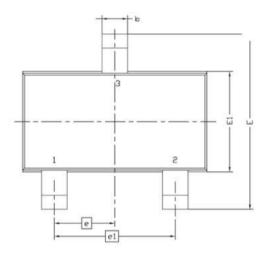
3,000/Reel

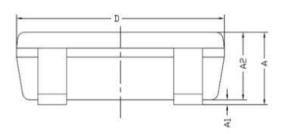


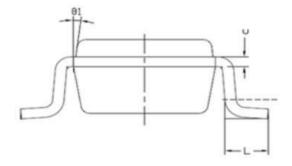


Graphic symbol









Cumbal	MILLIMETERS		
Symbol	MIN	MAX	
Α	0.8	1.2	
A1	0	0.1	
A2	0.7	1.1	
b	0.3	0.5	
С	0.1	0.2	
D	2.7	3.1	
E	2.6	3	
E1	1.4	1.8	
е	0.95 BSC		
e1	1.9 BSC		
L	0.3	0.6	
θ1	7° NOM		



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MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

MAXIMUM RATINGS (Ta=25°C unless otherwise noted)					
Symbol	Parameter	S9012	Unit		
V_{CBO}	Collector-Base Voltage	-40	Vdc		
V_{CEO}	Collector-Emitter Voltage	-30 Vdc			
$V_{\rm EBO}$	Emitter-Base Voltage	-5	Vdc		
I_{C}	Collector Current	-500	mAdc		
P _D	Collector Power Dissipation	300	mW		
Tj,Tstg	Junction and Storage Temperature	-55 to +150	°C		

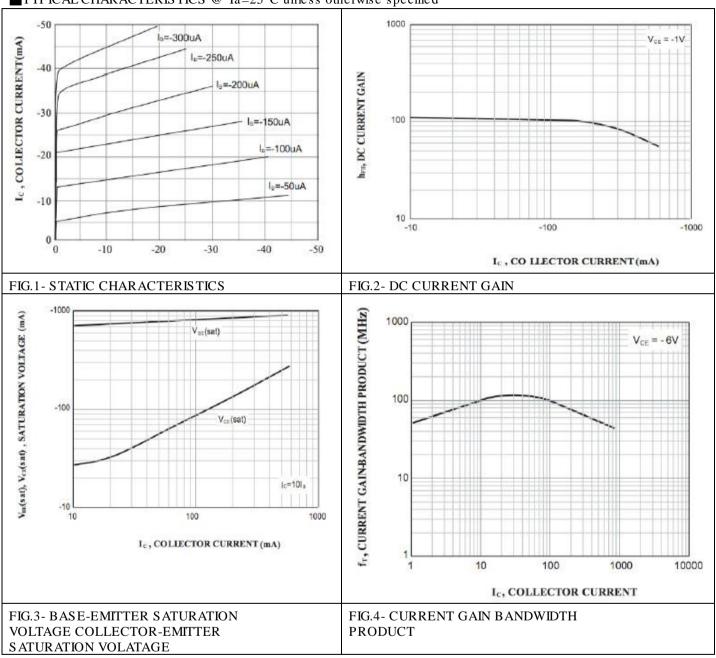
ELECTRIC	ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified						
Symbol	Parameter	Test Conditions	MIN	TYP	MAX	UNIT	
$V_{(BR)CBO}$	Collector-base breakdown voltage	$I_C = -100 \mu A$	-40			V	
V _{(BR)CEO}	Collector-emitter breakdown voltage	$I_C = -1 \text{ mA}$	-30			V	
$V_{(BR)EBO} \\$	Emitter-base breakdown voltage	$I_E = -100 \mu A$	-5			V	
I_{CBO}	Collector cut-off current	$V_{CB} = -35 \text{ V}$, $I_E = 0$			-0.1	uA	
I _{EBO}	Emitter cut-off current	$V_{EB} = -5 \text{ V}$, $I_C = 0$			-0.1	uA	
hFE(1)	DC current gain	$V_{CE} = -1 \text{ V}$, $I_C = -100 \text{ mA}$	70		400		
$V_{CE(sat)}$	Collector-emitter saturation voltage	$I_C = -500 \text{ mA}$, $I_B = -50 \text{ mA}$			-0.6	V	
V_{BE}	Base-Emitter Saturation Voltage	$V_{CE} = -1 \text{ V}, I_{C} = -100 \text{mA}$		-0.8	-1.0	V	
\mathbf{f}_{T}	Transition frequency	$V_{CE} = -6 \text{ V}$, $I_{C} = -20 \text{ mA}$	150	300		MHz	
C_{ob}	Collector output capacitance	V_{CB} = -6 V , I_E = 0 f = 1.0MHz		7	10	pF	

CLAS SIFICATION OF h _{FE}				
Rank	L	Н		
Rang	70-200	200-400		



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■TYPICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified





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